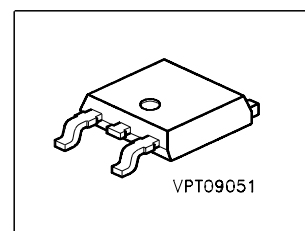


SIPMOS® Power-Transistor
Features

- P-Channel
- Enhancement mode
- Avalanche rated
- dv/dt rated
- 175°C operating temperature
- ° Pb-free lead plating; RoHS compliant
- ° Qualified according to AEC Q101

Product Summary

| | | | |
|----------------------------------|--------------|-------|----------|
| Drain source voltage | V_{DS} | -60 | V |
| Drain-source on-state resistance | $R_{DS(on)}$ | 0.13 | Ω |
| Continuous drain current | I_D | -18.6 | A |



| Type | Package |
|-------------|------------|
| SPD18P06P G | PG-TO252-3 |

| Pin 1 | PIN 2/4 | PIN 3 |
|-------|---------|-------|
| G | D | S |

Maximum Ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Value | Unit |
|--|-------------------|----------------|--------------------|
| Continuous drain current $T_C = 25\text{ °C}$ $T_C = 100\text{ °C}$ | I_D | -18.6 -13.2 | A |
| Pulsed drain current $T_C = 25\text{ °C}$ | I_D puls | -74.4 | |
| Avalanche energy, single pulse $I_D = -18.6\text{ A}$, $V_{DD} = -25\text{ V}$, $R_{GS} = 25\ \Omega$ | E_{AS} | 150 | mJ |
| Avalanche energy, periodic limited by T_{jmax} | E_{AR} | 8 | |
| Reverse diode dv/dt $I_S = -18.6\text{ A}$, $V_{DS} = -48\text{ V}$, $di/dt = 200\text{ A}/\mu\text{s}$, $T_{jmax} = 175\text{ °C}$ | dv/dt | 6 | kV/ μs |
| Gate source voltage | V_{GS} | ± 20 | V |
| Power dissipation $T_C = 25\text{ °C}$ | P_{tot} | 80 | W |
| Operating and storage temperature | T_j , T_{stg} | -55...+175 | $^{\circ}\text{C}$ |
| IEC climatic category; DIN IEC 68-1 | | 55/175/56 | |

Thermal Characteristics

| Parameter | Symbol | Values | | | Unit |
|---|------------|--------|------|----------|------|
| | | min. | typ. | max. | |
| Characteristics | | | | | |
| Thermal resistance, junction - case | R_{thJC} | - | - | 1.85 | K/W |
| Thermal resistance, junction - ambient, leaded | R_{thJA} | - | - | 100 | |
| SMD version, device on PCB: @ min. footprint @ 6 cm ² cooling area ¹⁾ | R_{thJA} | - | - | 75 50 | |

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|--|---------------|--------|-------------|------------|---------------|
| | | min. | typ. | max. | |
| Static Characteristics | | | | | |
| Drain- source breakdown voltage $V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$ | $V_{(BR)DSS}$ | -60 | - | - | V |
| Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = -1\text{ mA}$ | $V_{GS(th)}$ | -2.1 | -3 | -4 | |
| Zero gate voltage drain current $V_{DS} = -60\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 25\text{ °C}$ $V_{DS} = -60\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 150\text{ °C}$ | I_{DSS} | - | -0.1 -10 | -1 -100 | μA |
| Gate-source leakage current $V_{GS} = -20\text{ V}$, $V_{DS} = 0\text{ V}$ | I_{GSS} | - | -10 | -100 | nA |
| Drain-source on-state resistance $V_{GS} = -10\text{ V}$, $I_D = -13.2\text{ A}$ | $R_{DS(on)}$ | - | 0.1 | 0.13 | Ω |

¹Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|--|--------------|--------|------|------|------|
| | | min. | typ. | max. | |
| Dynamic Characteristics | | | | | |
| Transconductance $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = -13.2\text{ A}$ | g_{fs} | 4 | 8 | - | S |
| Input capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = -25\text{ V}$, $f = 1\text{ MHz}$ | C_{iss} | - | 690 | 860 | pF |
| Output capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = -25\text{ V}$, $f = 1\text{ MHz}$ | C_{oss} | - | 230 | 290 | |
| Reverse transfer capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = -25\text{ V}$, $f = 1\text{ MHz}$ | C_{rss} | - | 95 | 120 | |
| Turn-on delay time $V_{DD} = -30\text{ V}$, $V_{GS} = -10\text{ V}$, $I_D = -13.2\text{ A}$, $R_G = 2.7\text{ }\Omega$ | $t_{d(on)}$ | - | 12 | 18 | ns |
| Rise time $V_{DD} = -30\text{ V}$, $V_{GS} = -10\text{ V}$, $I_D = -13.2\text{ A}$, $R_G = 2.7\text{ }\Omega$ | t_r | - | 5.8 | 8.7 | |
| Turn-off delay time $V_{DD} = -30\text{ V}$, $V_{GS} = -10\text{ V}$, $I_D = -13.2\text{ A}$, $R_G = 2.7\text{ }\Omega$ | $t_{d(off)}$ | - | 24.5 | 37 | |
| Fall time $V_{DD} = -30\text{ V}$, $V_{GS} = -10\text{ V}$, $I_D = -13.2\text{ A}$, $R_G = 2.7\text{ }\Omega$ | t_f | - | 11 | 16.5 | |

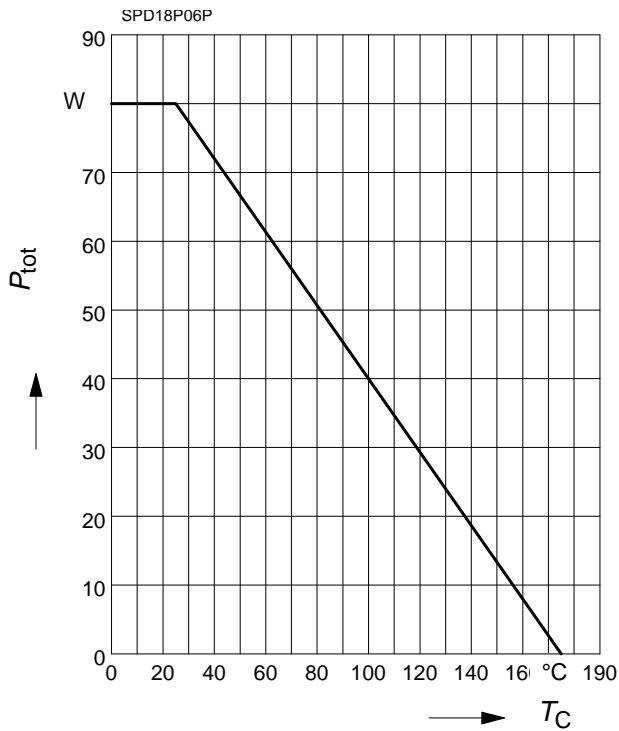
Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|---|-----------------|--------|-------|------|------|
| | | min. | typ. | max. | |
| Dynamic Characteristics | | | | | |
| Gate to source charge $V_{DD} = -48\text{ V}, I_D = -18.6\text{ A}$ | Q_{gs} | - | 4.4 | 6.6 | nC |
| Gate to drain charge $V_{DD} = -48\text{ V}, I_D = -18.6\text{ A}$ | Q_{gd} | - | 9.3 | 14 | |
| Gate charge total $V_{DD} = -48\text{ V}, I_D = -18.6\text{ A}, V_{GS} = 0\text{ to }-10\text{ V}$ | Q_g | - | 22 | 33 | |
| Gate plateau voltage $V_{DD} = -48\text{ V}, I_D = -18.6\text{ A}$ | $V_{(plateau)}$ | - | -5.56 | - | V |

| Parameter | Symbol | Values | | | Unit |
|--|----------|--------|------|-------|------|
| | | min. | typ. | max. | |
| Reverse Diode | | | | | |
| Inverse diode continuous forward current $T_C = 25\text{ °C}$ | I_S | - | - | -18.6 | A |
| Inverse diode direct current, pulsed $T_C = 25\text{ °C}$ | I_{SM} | - | - | -74.4 | |
| Inverse diode forward voltage $V_{GS} = 0\text{ V}, I_F = -18.6\text{ A}$ | V_{SD} | - | -1 | -1.33 | V |
| Reverse recovery time $V_R = -30\text{ V}, I_F = I_S, di_F/dt = 100\text{ A}/\mu\text{s}$ | t_{rr} | - | 70 | 105 | ns |
| Reverse recovery charge $V_R = -30\text{ V}, I_F = I_S, di_F/dt = 100\text{ A}/\mu\text{s}$ | Q_{rr} | - | 139 | 208 | nC |

Power dissipation

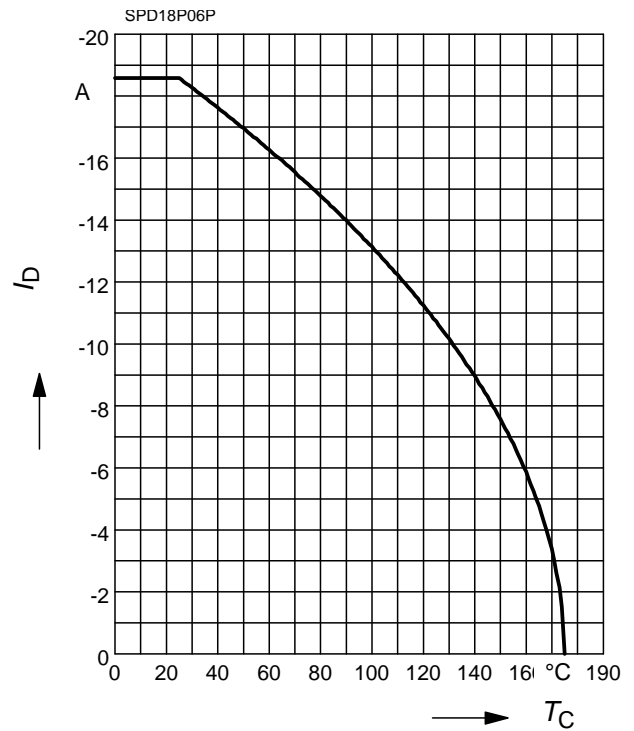
$P_{tot} = f(T_C)$



Drain current

$I_D = f(T_C)$

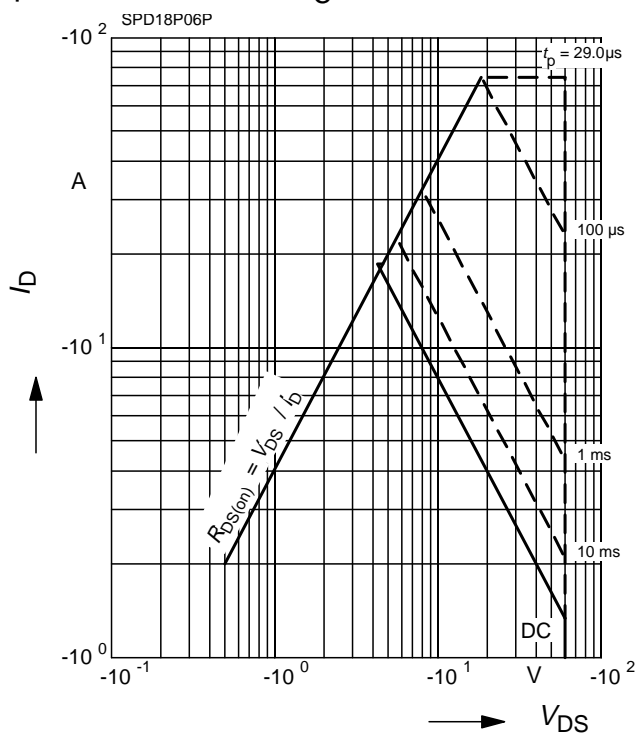
parameter: $V_{GS} \geq 10\text{ V}$



Safe operating area

$I_D = f(V_{DS})$

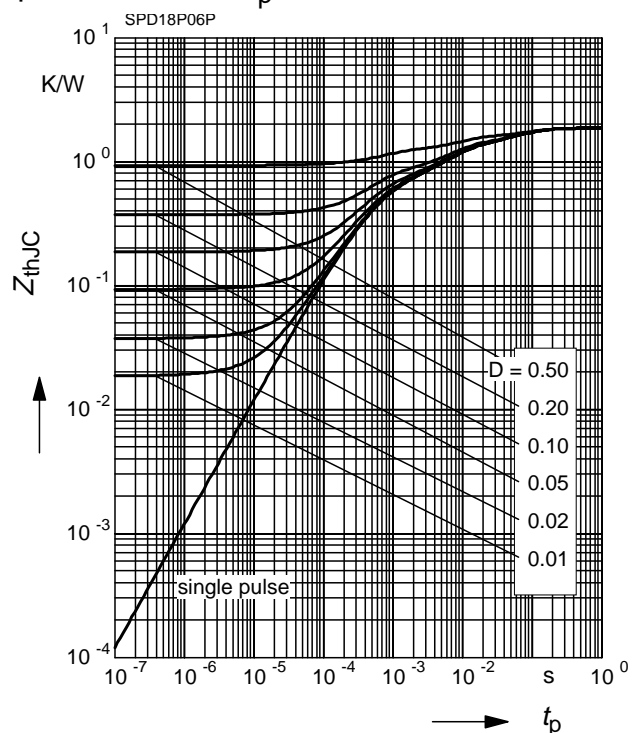
parameter: $D = 0, T_C = 25\text{ }^\circ\text{C}$



Transient thermal impedance

$Z_{thJC} = f(t_p)$

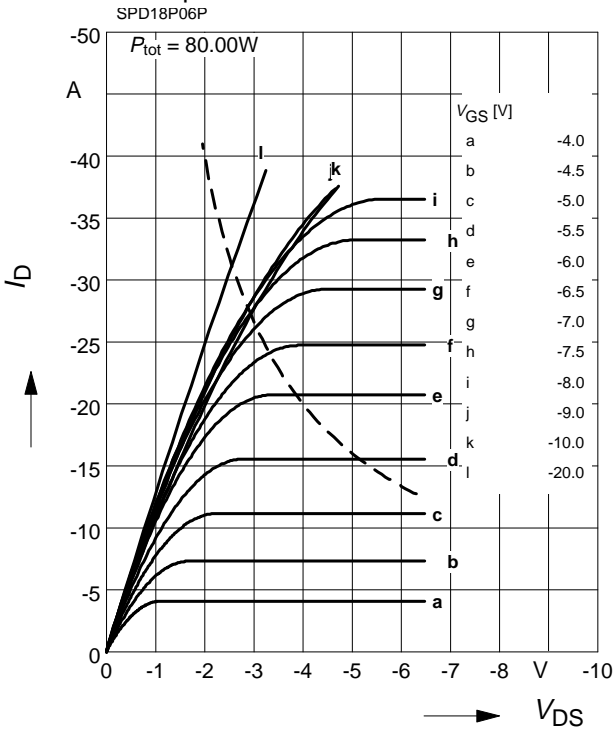
parameter: $D = t_p/T$



Typ. output characteristic

$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

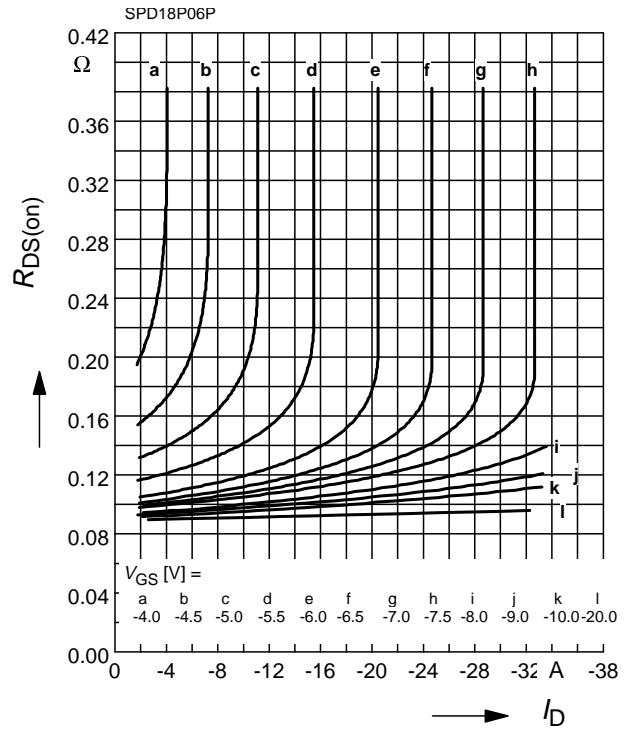
parameter: $t_p = 80 \mu\text{s}$



Typ. drain-source-on-resistance

$R_{DS(on)} = f(I_D)$

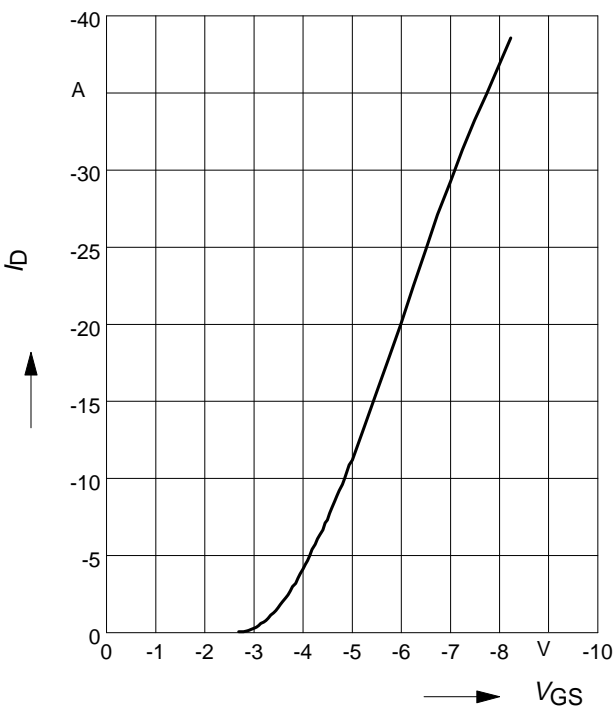
parameter: V_{GS}



Typ. transfer characteristics $I_D = f(V_{GS})$

$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

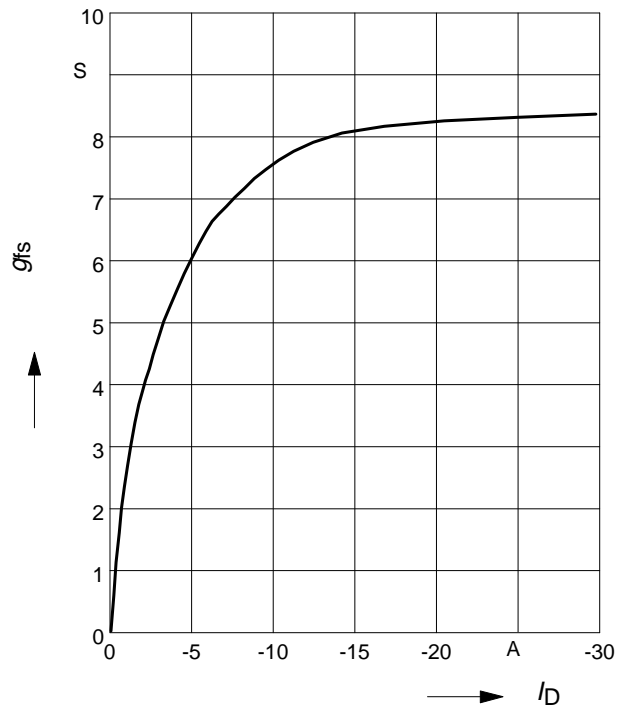
parameter: $t_p = 80 \mu\text{s}$



Typ. forward transconductance

$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$

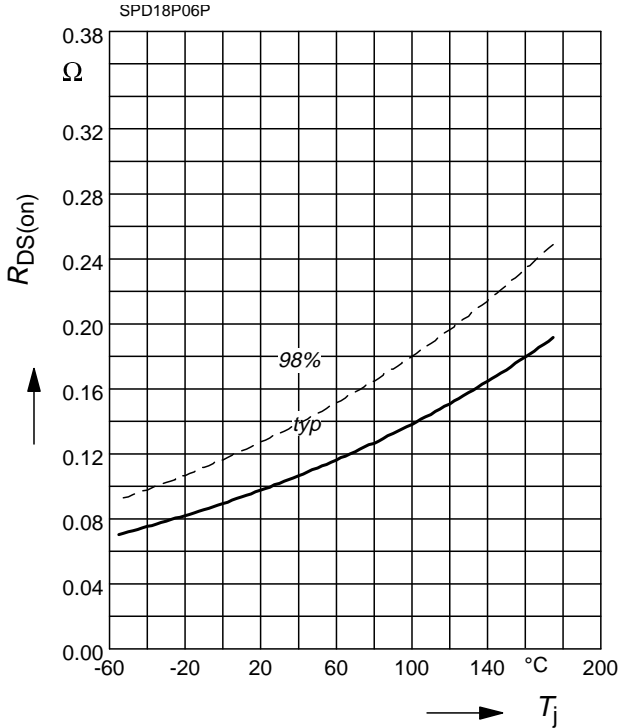
parameter: g_{fs}



Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

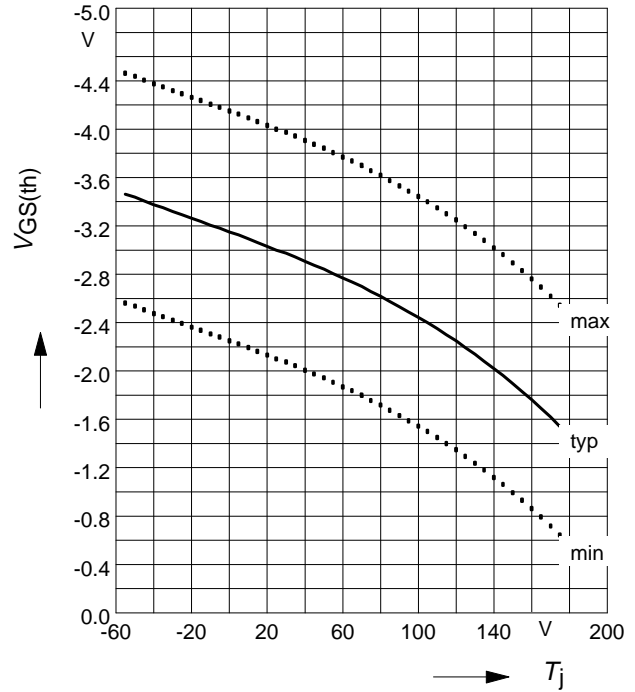
parameter: $I_D = -13.2 \text{ A}$, $V_{GS} = -10 \text{ V}$



Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

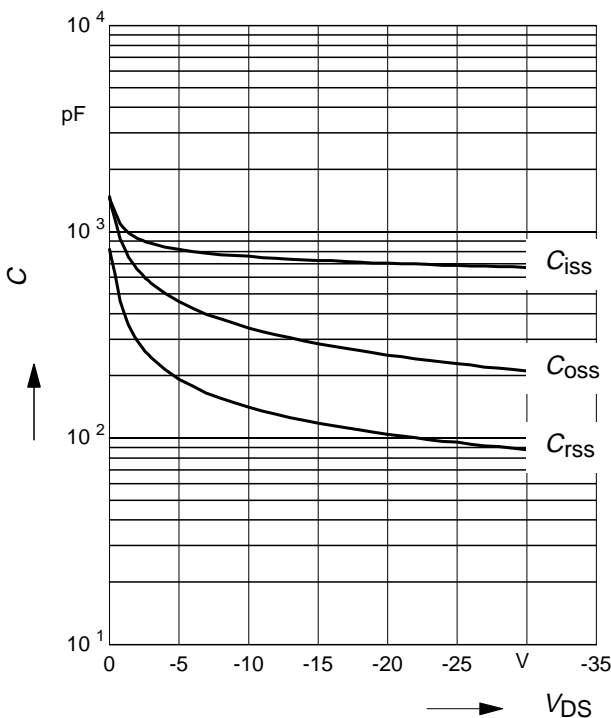
parameter: $V_{GS} = V_{DS}$, $I_D = -1 \text{ mA}$



Typ. capacitances

$$C = f(V_{DS})$$

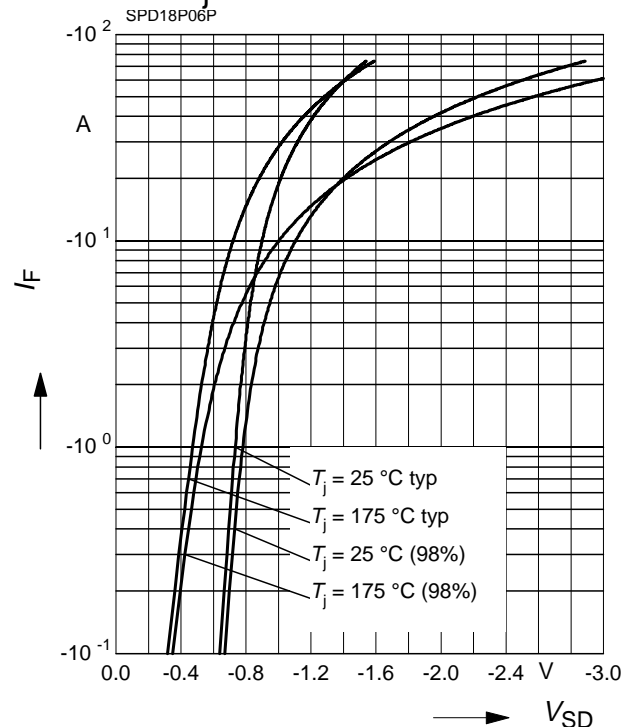
parameter: $V_{GS}=0\text{V}$, $f=1 \text{ MHz}$



Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

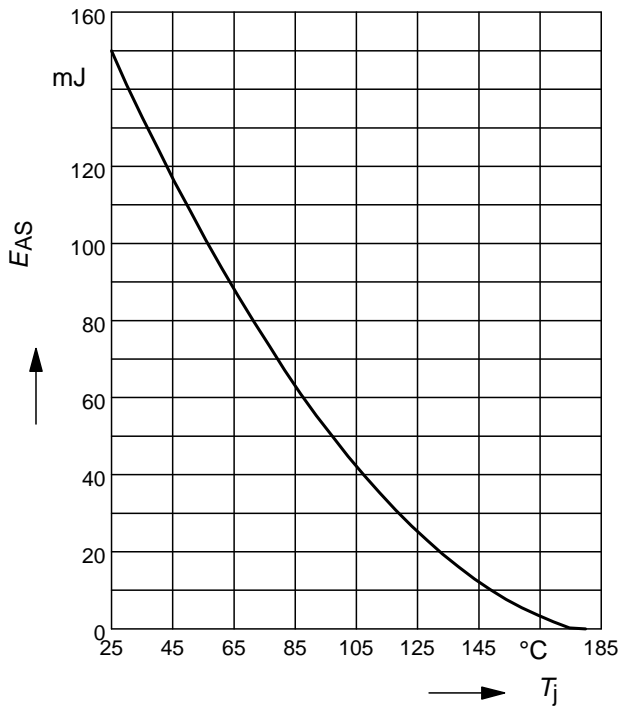
parameter: T_j , $t_p = 80 \mu\text{s}$



Avalanche energy

$$E_{AS} = f(T_j)$$

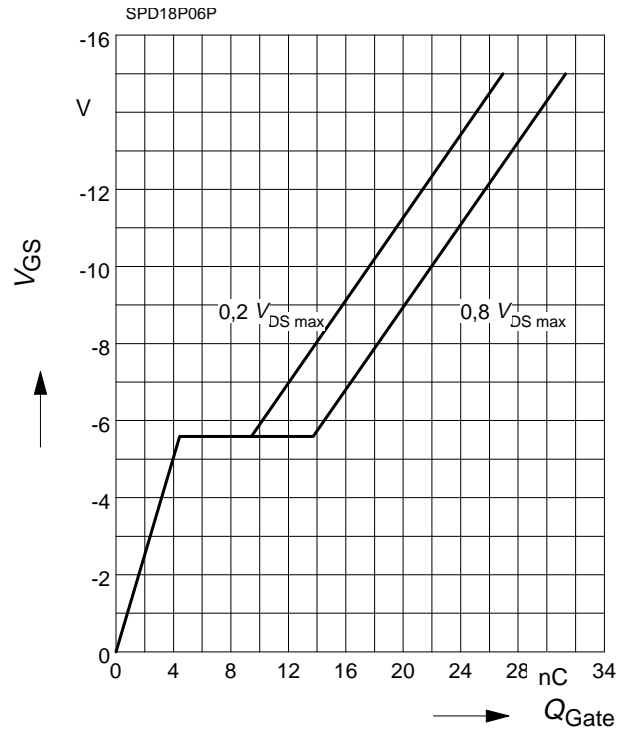
para.: $I_D = -18.6 \text{ A}$, $V_{DD} = -25 \text{ V}$, $R_{GS} = 25$



Typ. gate charge

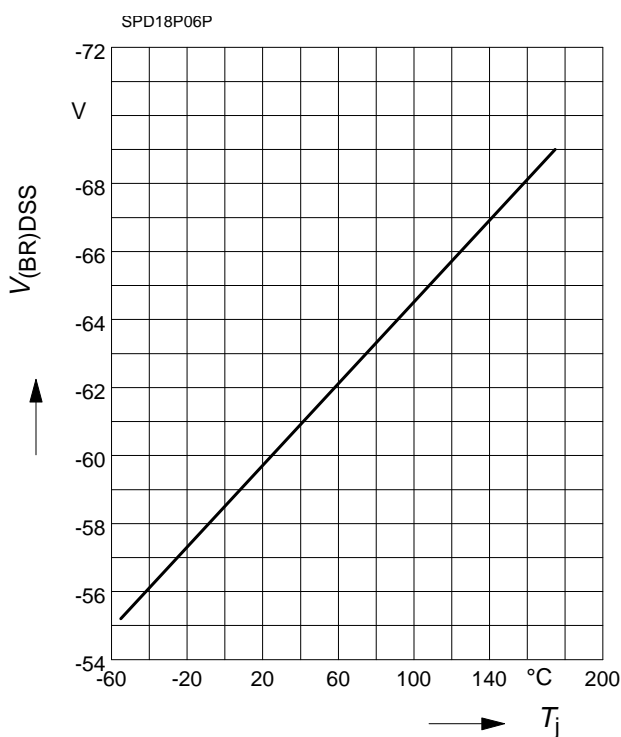
$$V_{GS} = f(Q_{Gate})$$

parameter: $I_D = -18.6 \text{ A}$ pulsed

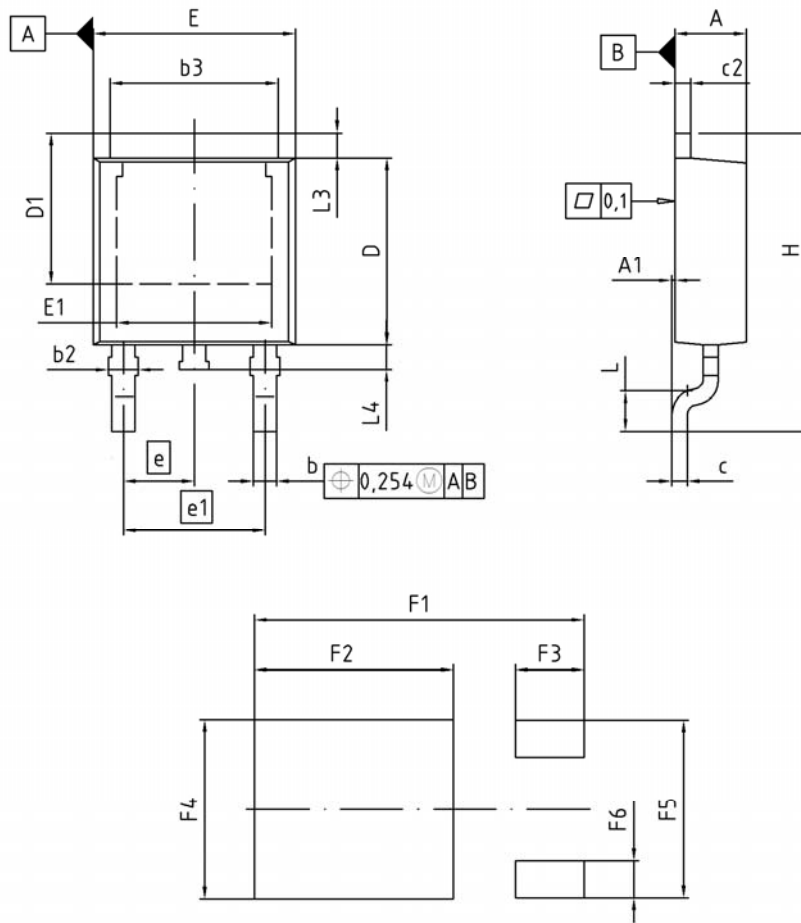


Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j)$$



Package outline: PG-TO252-3



| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|-------|--------|-------|
| | MIN | MAX | MIN | MAX |
| A | 2.16 | 2.41 | 0.085 | 0.095 |
| A1 | 0.00 | 0.15 | 0.000 | 0.006 |
| b | 0.64 | 0.89 | 0.025 | 0.035 |
| b2 | 0.65 | 1.15 | 0.026 | 0.045 |
| b3 | 5.00 | 5.50 | 0.197 | 0.217 |
| c | 0.46 | 0.60 | 0.018 | 0.024 |
| c2 | 0.46 | 0.98 | 0.018 | 0.039 |
| D | 5.97 | 6.22 | 0.235 | 0.245 |
| D1 | 5.02 | 5.84 | 0.198 | 0.230 |
| E | 6.40 | 6.73 | 0.252 | 0.265 |
| E1 | 4.70 | 5.21 | 0.185 | 0.205 |
| e | 2.29 | | 0.090 | |
| e1 | 4.57 | | 0.180 | |
| N | 3 | | 3 | |
| H | 9.40 | 10.48 | 0.370 | 0.413 |
| L | 1.18 | 1.70 | 0.046 | 0.067 |
| L3 | 0.90 | 1.25 | 0.035 | 0.049 |
| L4 | 0.51 | 1.00 | 0.020 | 0.039 |
| F1 | 10.50 | 10.70 | 0.413 | 0.421 |
| F2 | 6.30 | 6.50 | 0.248 | 0.256 |
| F3 | 2.10 | 2.30 | 0.083 | 0.091 |
| F4 | 5.70 | 5.90 | 0.224 | 0.232 |
| F5 | 5.66 | 5.86 | 0.223 | 0.231 |
| F6 | 1.10 | 1.30 | 0.043 | 0.051 |

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